TOSHIBA PHOTOCOUPLER GaAℓAs IRED & PHOTO-IC

TLP251F

INVERTER FOR AIR CONDITIONOR

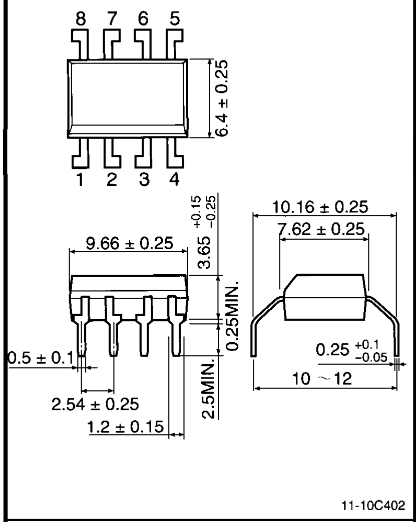
INDUCTION HEATING

TRANSISTOR INVERTER

POWER MOS FET GATE DRIVE

IGBT GATE DRIVE

Unit in mm



TOSHIBA 11-10C402

Weight : 0.54g

The Toshiba TLP251F consists of a GaAℓAs light emitting diode and a integrated photodetector.
This unit is 8-lead DIP package.
TLP251F is suitable for gate driving circuit of IGBT or power MOS FET. Especially TLP251 is capable of “direct” gate drive of lower power IGBTs. (~15A)

- Input Threshold Current : $I_F = 5$mA (Max.)
- Supply Current : 11mA (Max.)
- Supply Voltage : 10~35V
- Output Peak Current : ±0.4A (Max.)
- Switching Time : t_{pHL}, $t_{pLH} = 1\mu$s (Max.)
- Isolation Voltage : 2500V_{rms} (Min.)
- UL Recognized : UL1577, File No.E67349
- Option (D4) type

  VDE Approved : DIN VDE0884 / 06.92, Certificate No.87447
  Maximum Operating Insulation Voltage : 1140V_{PK}
  Highest Permissible Over Voltage : 6000V_{PK}

(Note 1) When a VDE0884 approved type is needed, please designate the “Option (D4)”

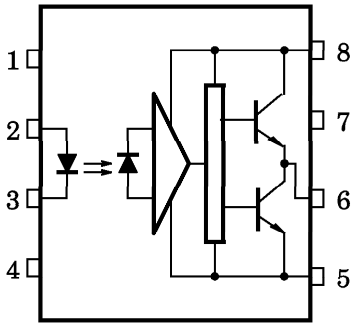
- Structural Parameter

  Creepage Distance : 8.0mm (Min.)
  Clearance : 8.0mm (Min.)

TRUTH TABLE

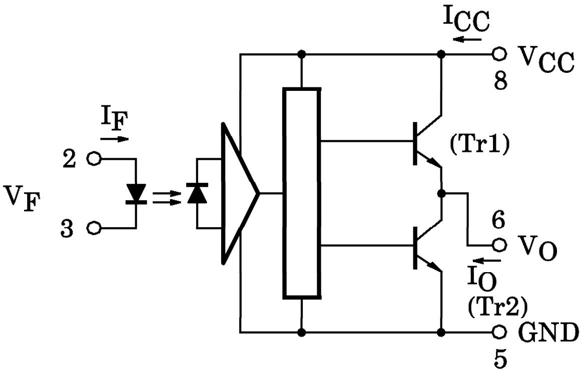
		Tr1	Tr2
Input LED	ON	ON	OFF
	OFF	OFF	ON

PIN CONFIGURATION (TOP VIEW)



1 : N.C.
2 : ANODE
3 : CATHODE
4 : N.C.
5 : GND
6 : V_O (OUTPUT)
7 : N.C.
8 : V_{CC}

SCHMATIC



(Note 2) A 0.1μF bypass capacitor must be connected between pin 8 and 5.

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